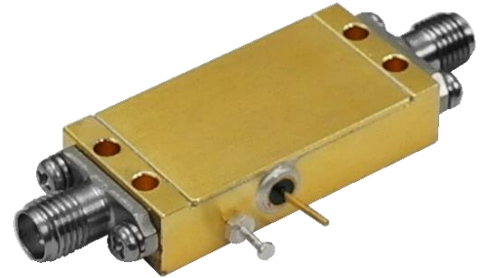


FEATURES:

Linear GaAsFET low noise hybrid design
 Suitable for all single channel composite modulation standards
 Designed for X-Band Radios, Radar, Telecomm, Satellite, Military, Space, MW links
 Also suitable for general lab, commercial & Mil applications
 Built-in regulator, sequencing, and protection circuits
 High efficiency, reliability, and ruggedness
ECCN Number: EAR99


ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification	Notes
Operating Frequency Range	9.37 - 10 GHz	
Linear Gain	33 dB Min	
Gain Flatness	1 dB p-p Max	
Output Power	+26 dBm Min	
Noise Figure	4.0 dB Max	
Input VSWR	1.5 : 1 Max	
Harmonics	-35 dBc Typ	
Operating Voltage	+8 VDC Nom	
Current Consumption	250 mA Typ	
Maximum Input Power	+3 dBm Max	
Gain Variation Over Temp	-0.05 dB/°C	

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions (L x W x H)	34.55 x 16.76 x 7.62 mm	
Connectors Input / Output	SMA Female	
Weight	15 gr.	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-40°C to 85 °C	
Storage Temperature Range	-55°C to +85 °C	Non-operating
Shock and Vibration	MIL-STD-810F	Designed to meet

OUTLINE DRAWING

